IN THE UNITED STATES PATENT AND TRADE MARKS OFFICE

Applicant:

R.C. Foss et al

Serial No:

07/680,747

Filed:

April 5, 1991

Title:

METHOD FOR DRAM SENSING CURRENT CONTROL

Art Unit:

2502

Examiner:

T. Dinh

Our File:

628.30050X00

The Commissioner of Patents and Trade Marks, Washington, D.C., 20231 U.S.A.

October 18, 1993

Dear Sir:

This is in response to the official action dated May 17th, 1993 in the above-identified application.

Please amend the claims as follows:

1. (Amended) A dynamic random access memory (DRAM) comprising:

- (a) a plurality of bit storage capacitors,
- (b) a folded bit line comprised of a complementary bit line pair for receiving charge stored on one of said capacitors, having bit line capacitance,
- (c) a sense amplifier having a pair of sense nodes for sensing a voltage differential across said sense nodes,
- (d) high resistance controllable current leakage UTALLUTE to said imperfect isolating means connecting said bit line to said

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